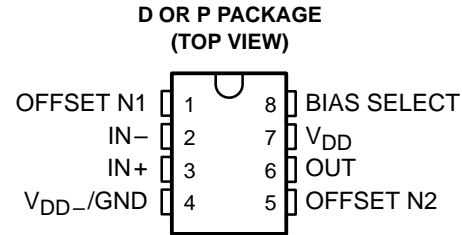


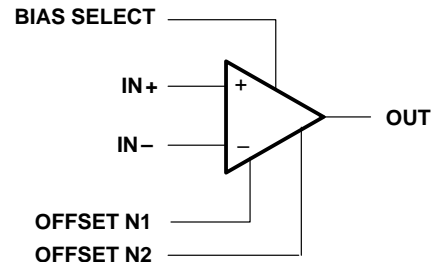
TLC251, TLC251A, TLC251B, TLC251Y LinCMOS™ PROGRAMMABLE LOW-POWER OPERATIONAL AMPLIFIERS

SLOS001F – JULY 1983 – REVISED MARCH 2001

- Wide Range of Supply Voltages
1.4-V to 16-V
- True Single-Supply Operation
- Common-Mode Input Voltage Range
Includes the Negative Rail
- Low Noise . . . 30 nV/√Hz Typ at 1-kHz
(High Bias)
- ESD Protection Exceeds 2000 V Per
MIL-STD-833C, Method 3015.1



symbol



description

The TLC251C, TLC251AC, and TLC251BC are low-cost, low-power programmable operational amplifiers designed to operate with single or dual supplies. Unlike traditional metal-gate CMOS operational amplifiers, these devices utilize Texas Instruments silicon-gate LinCMOS™ process, giving them stable input offset voltages without sacrificing the advantages of metal-gate CMOS.

This series of parts is available in selected grades of input offset voltage and can be nulled with one external potentiometer. Because the input common-mode range extends to the negative rail and the power consumption is extremely low, this family is ideally suited for battery-powered or energy-conserving applications. A bias-select pin can be used to program one of three ac performance and power-dissipation levels to suit the application. The series features operation down to a 1.4-V supply and is stable at unity gain.

These devices have internal electrostatic-discharge (ESD) protection circuits that prevent catastrophic failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.1. However, care should be exercised in handling these devices as exposure to ESD may result in a degradation of the device parametric performance.

Because of the extremely high input impedance and low input bias and offset currents, applications for the TLC251C series include many areas that have previously been limited to BIFET and NFET product types. Any circuit using high-impedance elements and requiring small offset errors is a good candidate for cost-effective use of these devices. Many features associated with bipolar technology are available with LinCMOS™ operational amplifiers without the power penalties of traditional bipolar devices. Remote and inaccessible equipment applications are possible using the low-voltage and low-power capabilities of the TLC251C series.

In addition, by driving the bias-select input with a logic signal from a microprocessor, these operational amplifiers can have software-controlled performance and power consumption. The TLC251C series is well suited to solve the difficult problems associated with single battery and solar cell-powered applications.

The TLC251C series is characterized for operation from 0°C to 70°C.

AVAILABLE OPTIONS

T _A	V _{IOMax} AT 25°C	PACKAGED DEVICES		CHIP FORM (Y)
		SMALL OUTLINE (D)	PLASTIC DIP (P)	
0°C to 70°C	10 mV	TLC251CD	TLC251CP	TLC251Y
	5 mV	TLC251ACD	TLC251ACP	—
	2 mV	TLC251BCD	TLC251BCP	—

The D package is available taped and reeled. Add the suffix R to the device type (e.g., TLC251CDR). Chips are tested at 25°C.

LinCMOS is a trademark of Texas Instruments.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

 **TEXAS
INSTRUMENTS**

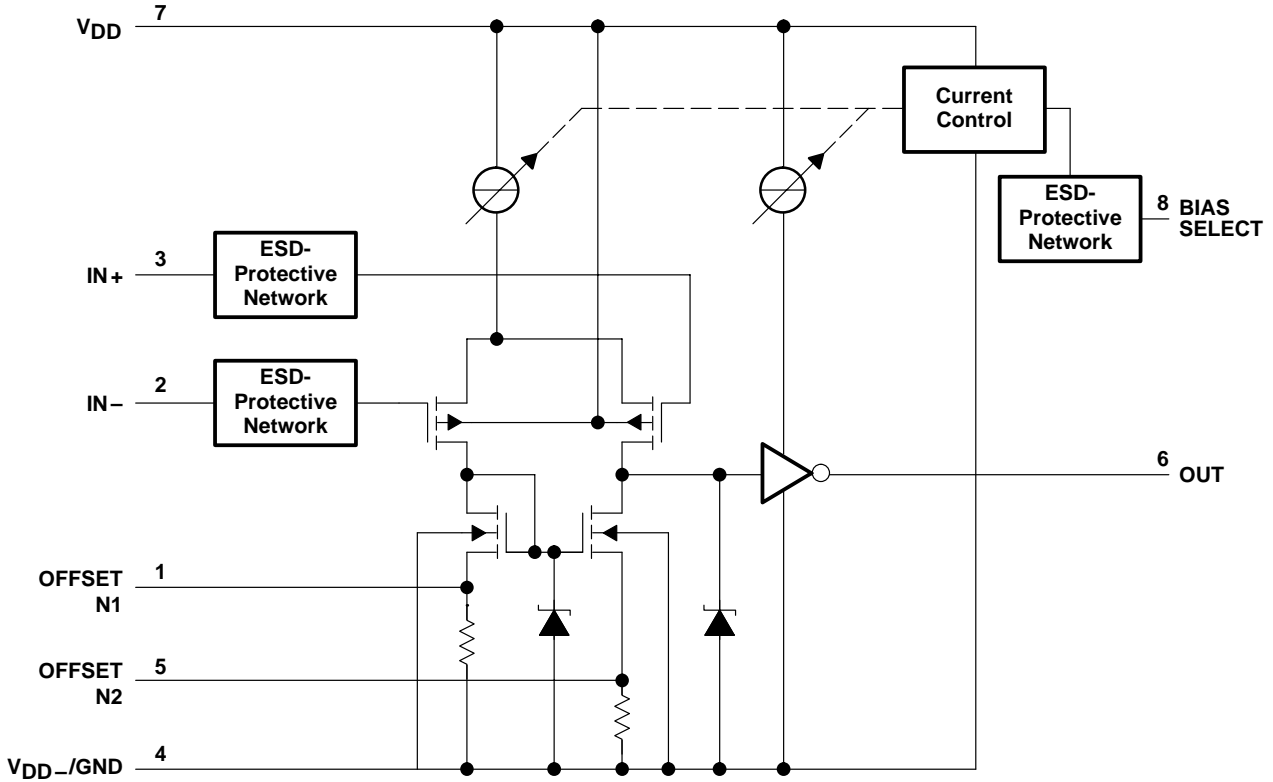
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Copyright © 2001, Texas Instruments Incorporated

TLC251, TLC251A, TLC251B, TLC251Y LinCMOS™ PROGRAMMABLE LOW-POWER OPERATIONAL AMPLIFIERS

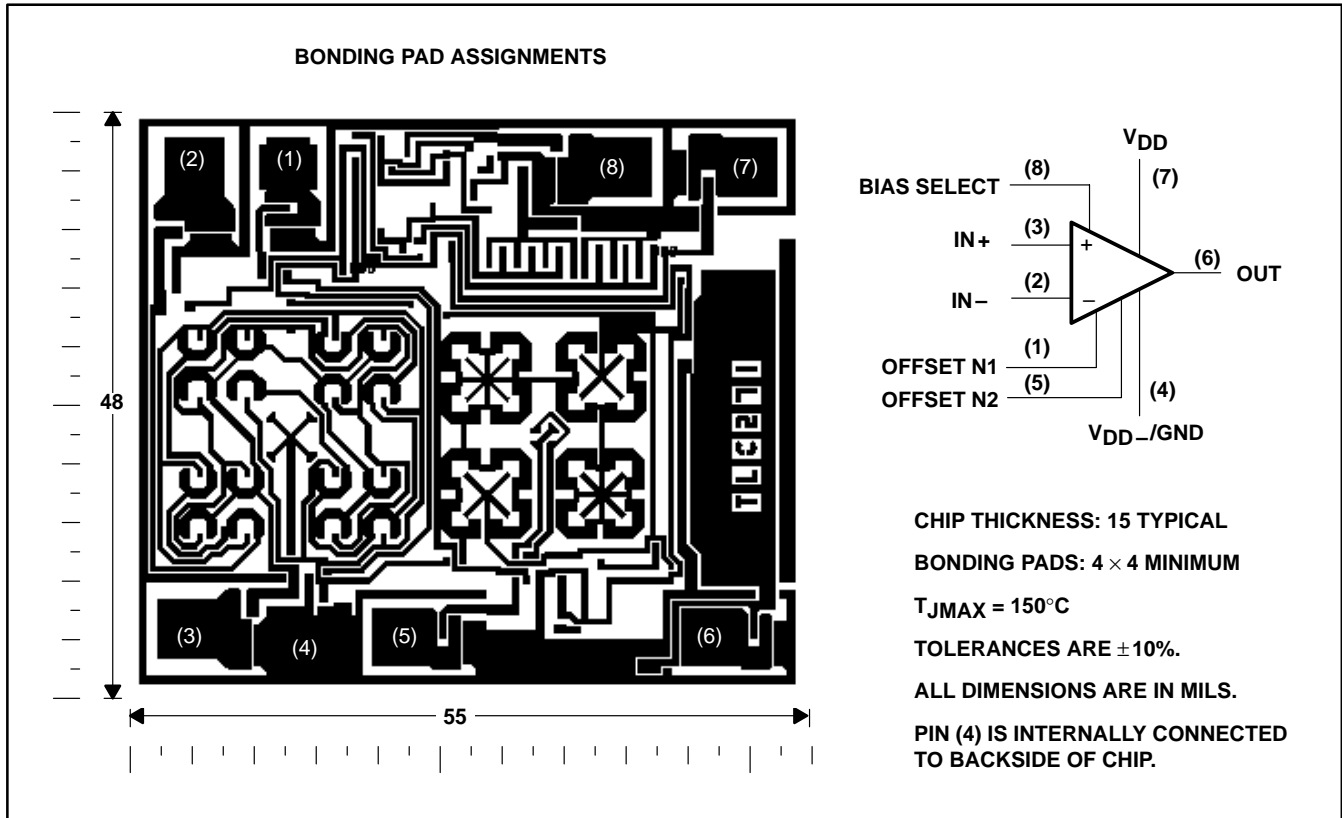
SLOS001F – JULY 1983 – REVISED MARCH 2001

schematic



TLC251Y chip information

These chips, properly assembled, display characteristics similar to the TLC251C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



TLC251, TLC251A, TLC251B, TLC251Y LinCMOS™ PROGRAMMABLE LOW-POWER OPERATIONAL AMPLIFIERS

SLOS001F – JULY 1983 – REVISED MARCH 2001

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V_{DD} (see Note 1)	18 V
Differential input voltage, V_{ID} (see Note 2)	± 18 V
Input voltage range, V_I (any input)	-0.3 V to 18 V
Duration of short circuit at (or below) 25°C free-air temperature (see Note 3)	unlimited
Continuous total dissipation	See Dissipation Rating Table
Operating free-air temperature range, T_A	0°C to 70°C
Storage temperature range	-65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to V_{DD-}/GND .
2. Differential voltages are at $IN+$ with respect to $IN-$.
3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 70^\circ\text{C}$ POWER RATING
D	725 mW	5.8 mW/°C	464 mW
P	1000 mW	8.0 mW/°C	640 mW

recommended operating conditions

	MIN	MAX	UNIT
Supply voltage, V_{DD}	1.4	16	V
Common-mode input voltage, V_{IC}	$V_{DD} = 1.4$ V	0	0.2
	$V_{DD} = 5$ V	-0.2	4
	$V_{DD} = 10$ V	-0.2	9
	$V_{DD} = 16$ V	-0.2	14
Operating free-air temperature, T_A	0	70	°C
Bias-select voltage	See Application Information		



TLC251, TLC251A, TLC251B, TLC251Y LinCMOS™ PROGRAMMABLE LOW-POWER OPERATIONAL AMPLIFIERS

SLOS001F – JULY 1983 – REVISED MARCH 2001

HIGH-BIAS MODE

electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS	T _A [†]	TLC251C, TLC251AC, TLC251BC						UNIT	
				V _{DD} = 5 V			V _{DD} = 10 V				
				MIN	TYP	MAX	MIN	TYP	MAX		
V _{IO}	Input offset voltage	TLC251C	25°C	1.1		10	1.1		10	mV	
			Full range				12				
			TLC251AC	25°C	0.9		5	0.9			5
				Full range				6.5			
			TLC251BC	25°C	0.34		2	0.39			2
				Full range				3			
α _{VIO}	Average temperature coefficient of input offset voltage		25°C to 70°C	1.8		2			μV/°C		
I _{IO}	Input offset current (see Note 4)	V _O = V _{DD} /2, V _{IC} = V _{DD} /2	25°C	0.1		60	0.1		60	pA	
			70°C	7		300	7		300		
I _{IB}	Input bias current (see Note 4)	V _O = V _{DD} /2, V _{IC} = V _{DD} /2	25°C	0.6		60	0.7		60	pA	
			70°C	40		600	50		600		
V _{ICR}	Common-mode input voltage range (see Note 5)		25°C	-0.2 to 4	-0.3 to 4.2		-0.2 to 9	-0.3 to 9.2		V	
			Full range	-0.2 to 3.5		-0.2 to 8.5				V	
V _{OH}	High-level output voltage	V _{ID} = 100 mV, R _L = 10 kΩ	25°C	3.2		3.8	8		8.5	V	
			0°C	3		3.8	7.8		8.5		
			70°C	3		3.8	7.8		8.4		
V _{OL}	Low-level output voltage	V _{ID} = -100 mV, I _{OL} = 0	25°C	0		50	0		50	mV	
			0°C	0		50	0		50		
			70°C	0		50	0		50		
A _{VD}	Large-signal differential voltage amplification	R _L = 10 kΩ, See Note 6	25°C	5		23	10		36	V/mV	
			0°C	4		27	7.5		42		
			70°C	4		20	7.5		32		
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin}	25°C	65		80	65		85	dB	
			0°C	60		84	60		88		
			70°C	60		85	60		88		
k _{SVR}	Supply-voltage rejection ratio (ΔV _{DD} /ΔV _{IO})	V _{DD} = 5 V to 10 V, V _O = 1.4 V	25°C	65		95	65		95	dB	
			0°C	60		94	60		94		
			70°C	60		96	60		96		
I _{I(SEL)}	Input current (BIAS SELECT)	V _{I(SEL)} = 0	25°C	-1.4		-1.9			μA		
I _{DD}	Supply current	V _O = V _{DD} /2, V _{IC} = V _{DD} /2, No load	25°C	675		1600	950		2000	μA	
			0°C	775		1800	1125		2200		
			70°C	575		1300	750		1700		

[†] Full range is 0°C to 70°C.

- NOTES:
4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.
 5. This range also applies to each input individually.
 6. At V_{DD} = 5 V, V_O = 0.25 V to 2 V; at V_{DD} = 10 V, V_O = 1 V to 6 V.



TLC251, TLC251A, TLC251B, TLC251Y
LinCMOS™ PROGRAMMABLE
LOW-POWER OPERATIONAL AMPLIFIERS

SLOS001F – JULY 1983 – REVISED MARCH 2001

HIGH-BIAS MODE

operating characteristics, $V_{DD} = 5\text{ V}$

PARAMETER	TEST CONDITIONS	T_A	TLC251C, TLC251AC, TLC251BC			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain	$R_L = 10\text{ k}\Omega$, $C_L = 20\text{ pF}$	$V_{I(PP)} = 1\text{ V}$	25°C	3.6		V/ μ s
			0°C	4		
			70°C	3		
		$V_{I(PP)} = 2.5\text{ V}$	25°C	2.9		
			0°C	3.1		
			70°C	2.5		
V_n Equivalent input noise voltage	$f = 1\text{ kHz}$, $R_S = 20\ \Omega$	25°C	25		nV/ $\sqrt{\text{Hz}}$	
B_{OM} Maximum output-swing bandwidth	$V_O = V_{OH}$, $C_L = 20\text{ pF}$, $R_L = 10\text{ k}\Omega$	25°C	320		kHz	
		0°C	340			
		70°C	260			
B_1 Unity-gain bandwidth	$V_I = 10\text{ mV}$, $C_L = 20\text{ pF}$	25°C	1.7		MHz	
		0°C	2			
		70°C	1.3			
ϕ_m Phase margin	$V_I = 10\text{ mV}$, $f = B_1$, $C_L = 20\text{ pF}$	25°C	46°			
		0°C	47°			
		70°C	44°			

operating characteristics, $V_{DD} = 10\text{ V}$

PARAMETER	TEST CONDITIONS	T_A	TLC251C, TLC251AC, TLC251BC			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain	$R_L = 10\text{ k}\Omega$, $C_L = 20\text{ pF}$	$V_{I(PP)} = 1\text{ V}$	25°C	5.3		V/ μ s
			0°C	5.9		
			70°C	4.3		
		$V_{I(PP)} = 5.5\text{ V}$	25°C	4.6		
			0°C	5.1		
			70°C	3.8		
V_n Equivalent input noise voltage	$f = 1\text{ kHz}$, $R_S = 20\ \Omega$	25°C	25		nV/ $\sqrt{\text{Hz}}$	
B_{OM} Maximum output-swing bandwidth	$V_O = V_{OH}$, $C_L = 20\text{ pF}$, $R_L = 10\text{ k}\Omega$	25°C	200		kHz	
		0°C	220			
		70°C	140			
B_1 Unity-gain bandwidth	$V_I = 10\text{ mV}$, $C_L = 20\text{ pF}$	25°C	2.2		MHz	
		0°C	2.5			
		70°C	1.8			
ϕ_m Phase margin	$V_I = 10\text{ mV}$, $f = B_1$, $C_L = 20\text{ pF}$	25°C	49°			
		0°C	50°			
		70°C	46°			



TLC251, TLC251A, TLC251B, TLC251Y
 LinCMOS™ PROGRAMMABLE
 LOW-POWER OPERATIONAL AMPLIFIERS

SLOS001F – JULY 1983 – REVISED MARCH 2001

MEDIUM-BIAS MODE

electrical characteristics at specified free-air temperature

PARAMETER	TEST CONDITIONS	T _A †	TLC251C, TLC251AC, TLC251BC						UNIT
			V _{DD} = 5 V			V _{DD} = 10 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO} Input offset voltage	TLC251C TLC251AC TLC251BC	V _O = 1.4 V, V _{IC} = 0 V, R _S = 50 Ω, R _L = 10 kΩ	25°C	1.1 10		1.1 10		mV	
			Full range	12		12			
			25°C	0.9 5		0.9 5			
			Full range	6.5		6.5			
			25°C	0.34 2		0.39 2			
Full range	3		3						
α _{VIO} Average temperature coefficient of input offset voltage		25°C to 70°C	1.7			2.1		μV/°C	
I _{IO} Input offset current (see Note 4)	V _O = V _{DD} /2, V _{IC} = V _{DD} /2	25°C	0.1 60		0.1 60		pA		
		70°C	7 300		7 300				
I _{IB} Input bias current (see Note 4)	V _O = V _{DD} /2, V _{IC} = V _{DD} /2	25°C	0.6 60		0.7 60		pA		
		70°C	40 600		50 600				
V _{ICR} Common-mode input voltage range (see Note 5)		25°C	-0.2 to 4	-0.3 to 4.2	-0.2 to 9	-0.3 to 9.2	V		
		Full range	-0.2 to 3.5		-0.2 to 8.5		V		
V _{OH} High-level output voltage	V _{ID} = 100 mV, R _L = 10 kΩ	25°C	3.2	3.9	8	8.7	V		
		0°C	3	3.9	7.8	8.7			
		70°C	3	4	7.8	8.7			
V _{OL} Low-level output voltage	V _{ID} = -100 mV, I _{OL} = 0	25°C	0 50		0 50		mV		
		0°C	0 50		0 50				
		70°C	0 50		0 50				
A _{VD} Large-signal differential voltage amplification	R _L = 10 kΩ, See Note 6	25°C	25	170	25	275	V/mV		
		0°C	15	200	15	320			
		70°C	15	140	15	230			
CMRR Common-mode rejection ratio	V _{IC} = V _{ICRmin}	25°C	65	91	65	94	dB		
		0°C	60	91	60	94			
		70°C	60	92	60	94			
k _{SVR} Supply-voltage rejection ratio (ΔV _{DD} /ΔV _{IO})	V _{DD} = 5 V to 10 V, V _O = 1.4 V	25°C	70	93	70	93	dB		
		0°C	60	92	60	92			
		70°C	60	94	60	94			
I _{I(SEL)} Input current (BIAS SELECT)	V _{I(SEL)} = V _{DD} /2	25°C	-130		-160		nA		
I _{DD} Supply current	V _O = V _{DD} /2, V _{IC} = V _{DD} /2, No load	25°C	105	280	143	300	μA		
		0°C	125	320	173	400			
		70°C	85	220	110	280			

† Full range is 0°C to 70°C.

- NOTES:
- The typical values of input bias current and input offset current below 5 pA were determined mathematically.
 - This range also applies to each input individually.
 - At V_{DD} = 5 V, V_O = 0.25 V to 2 V; at V_{DD} = 10 V, V_O = 1 V to 6 V.



TLC251, TLC251A, TLC251B, TLC251Y
LinCMOS™ PROGRAMMABLE
LOW-POWER OPERATIONAL AMPLIFIERS

SLOS001F – JULY 1983 – REVISED MARCH 2001

MEDIUM-BIAS MODE

operating characteristics, $V_{DD} = 5\text{ V}$

PARAMETER	TEST CONDITIONS	T _A	TLC251C, TLC251AC, TLC251BC			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain	R _L = 100 k Ω , C _L = 20 pF	V _{I(PP)} = 1 V	25°C	0.43		V/ μ s
			0°C	0.46		
			70°C	0.36		
		V _{I(PP)} = 2.5 V	25°C	0.40		
			0°C	0.43		
			70°C	0.34		
V _n Equivalent input noise voltage	f = 1 kHz, R _S = 20 Ω	25°C	32		nV/ $\sqrt{\text{Hz}}$	
B _{OM} Maximum output-swing bandwidth	V _O = V _{OH} , C _L = 20 pF, R _L = 100 k Ω	25°C	55		kHz	
		0°C	60			
		70°C	50			
B ₁ Unity-gain bandwidth	V _I = 10 mV, C _L = 20 pF	25°C	525		kHz	
		0°C	600			
		70°C	400			
ϕ_m Phase margin	V _I = 10 mV, f = B ₁ , C _L = 20 pF	25°C	40°			
		0°C	41°			
		70°C	39°			

operating characteristics, $V_{DD} = 10\text{ V}$

PARAMETER	TEST CONDITIONS	T _A	TLC251C, TLC251AC, TLC251BC			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain	R _L = 100 k Ω , C _L = 20 pF	V _{I(PP)} = 1 V	25°C	0.62		V/ μ s
			0°C	0.67		
			70°C	0.51		
		V _{I(PP)} = 5.5 V	25°C	0.56		
			0°C	0.61		
			70°C	0.46		
V _n Equivalent input noise voltage	f = 1 kHz, R _S = 20 Ω	25°C	32		nV/ $\sqrt{\text{Hz}}$	
B _{OM} Maximum output-swing bandwidth	V _O = V _{OH} , C _L = 20 pF, R _L = 100 k Ω	25°C	35		kHz	
		0°C	40			
		70°C	30			
B ₁ Unity-gain bandwidth	V _I = 10 mV, C _L = 20 pF	25°C	635		kHz	
		0°C	710			
		70°C	510			
ϕ_m Phase margin	V _I = 10 mV, f = B ₁ , C _L = 20 pF	25°C	43°			
		0°C	44°			
		70°C	42°			



POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

TLC251, TLC251A, TLC251B, TLC251Y
LinCMOS™ PROGRAMMABLE
LOW-POWER OPERATIONAL AMPLIFIERS

SLOS001F – JULY 1983 – REVISED MARCH 2001

LOW-BIAS MODE

electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS	T _A †	TLC251C, TLC251AC, TLC251BC						UNIT	
				V _{DD} = 5 V			V _{DD} = 10 V				
				MIN	TYP	MAX	MIN	TYP	MAX		
V _{IO}	Input offset voltage	TLC251C	25°C	1.1		10	1.1		10	mV	
			Full range			12			12		
			TLC251AC	25°C	0.9		5	0.9			5
				Full range			6.5				6.5
			TLC251BC	25°C	0.24		2	0.26			2
Full range				3			3				
α _{VIO}	Average temperature coefficient of input offset voltage		25°C to 70°C	1.1			1		μV/°C		
I _{IO}	Input offset current (see Note 4)	V _O = V _{DD} /2, V _{IC} = V _{DD} /2	25°C	0.1		60	0.1		60	pA	
			70°C	7		300	7		300		
I _{IB}	Input bias current (see Note 4)	V _O = V _{DD} /2, V _{IC} = V _{DD} /2	25°C	0.6		60	0.7		60	pA	
			70°C	40		600	50		600		
V _{ICR}	Common-mode input voltage range (see Note 5)		25°C	-0.2 to 4	-0.3 to 4.2		-0.2 to 9	-0.3 to 9.2	V		
			Full range	-0.2 to 3.5			-0.2 to 8.5		V		
V _{OH}	High-level output voltage	V _{ID} = 100 mV, R _L = 1 MΩ	25°C	3.2	4.1		8	8.9	V		
			0°C	3	4.1		7.8	8.9			
			70°C	3	4.2		7.8	8.9			
V _{OL}	Low-level output voltage	V _{ID} = -100 mV, I _{OL} = 0	25°C	0		50	0		50	mV	
			0°C	0		50	0		50		
			70°C	0		50	0		50		
A _{VD}	Large-signal differential voltage amplification	R _L = 1 MΩ, See Note 6	25°C	50	520		50	870	V/mV		
			0°C	50	700		50	1030			
			70°C	50	380		50	660			
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin}	25°C	65	94		65	97	dB		
			0°C	60	95		60	97			
			70°C	60	95		60	97			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{DD} /ΔV _{IO})	V _{DD} = 5 V to 10 V, V _O = 1.4 V	25°C	70	97		70	97	dB		
			0°C	60	97		60	97			
			70°C	60	98		60	98			
I _{I(SEL)}	Input current (BIAS SELECT)	V _{I(SEL)} = V _{DD}	25°C	65			95		nA		
I _{DD}	Supply current	V _O = V _{DD} /2, V _{IC} = V _{DD} /2, No load	25°C	10		17	14		23	μA	
			0°C	12		21	18		33		
			70°C	8		14	11		20		

† Full range is 0°C to 70°C.

- NOTES:
4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.
 5. This range also applies to each input individually.
 6. At V_{DD} = 5 V, V_O = 0.25 V to 2 V; at V_{DD} = 10 V, V_O = 1 V to 6 V.



TLC251, TLC251A, TLC251B, TLC251Y
LinCMOS™ PROGRAMMABLE
LOW-POWER OPERATIONAL AMPLIFIERS

SLOS001F – JULY 1983 – REVISED MARCH 2001

LOW-BIAS MODE

operating characteristics, $V_{DD} = 5\text{ V}$

PARAMETER	TEST CONDITIONS	T_A	TLC251C, TLC251AC, TLC251BC			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain	$R_L = 1\text{ M}\Omega$, $C_L = 20\text{ pF}$	$V_{I(PP)} = 1\text{ V}$	25°C	0.03		V/ μ s
			0°C	0.04		
			70°C	0.03		
		$V_{I(PP)} = 2.5\text{ V}$	25°C	0.03		
			0°C	0.03		
			70°C	0.02		
V_n Equivalent input noise voltage	$f = 1\text{ kHz}$, $R_S = 20\ \Omega$	25°C	68		nV/ $\sqrt{\text{Hz}}$	
B_{OM} Maximum output-swing bandwidth	$V_O = V_{OH}$, $C_L = 20\text{ pF}$, $R_L = 1\text{ M}\Omega$	25°C	5		kHz	
		0°C	6			
		70°C	4.5			
B_1 Unity-gain bandwidth	$V_I = 10\text{ mV}$, $C_L = 20\text{ pF}$	25°C	85		kHz	
		0°C	100			
		70°C	65			
ϕ_m Phase margin	$V_I = 10\text{ mV}$, $f = B_1$, $C_L = 20\text{ pF}$	25°C	34°			
		0°C	36°			
		70°C	30°			

operating characteristics, $V_{DD} = 10\text{ V}$

PARAMETER	TEST CONDITIONS	T_A	TLC251C, TLC251AC, TLC251BC			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain	$R_L = 1\text{ M}\Omega$, $C_L = 20\text{ pF}$	$V_{I(PP)} = 1\text{ V}$	25°C	0.05		V/ μ s
			0°C	0.05		
			70°C	0.04		
		$V_{I(PP)} = 5.5\text{ V}$	25°C	0.04		
			0°C	0.05		
			70°C	0.04		
V_n Equivalent input noise voltage	$f = 1\text{ kHz}$, $R_S = 20\ \Omega$	25°C	68		nV/ $\sqrt{\text{Hz}}$	
B_{OM} Maximum output-swing bandwidth	$V_O = V_{OH}$, $C_L = 20\text{ pF}$, $R_L = 1\text{ M}\Omega$	25°C	1		kHz	
		0°C	1.3			
		70°C	0.9			
B_1 Unity-gain bandwidth	$V_I = 10\text{ mV}$, $C_L = 20\text{ pF}$	25°C	110		kHz	
		0°C	125			
		70°C	90			
ϕ_m Phase margin	$V_I = 10\text{ mV}$, $f = B_1$, $C_L = 20\text{ pF}$	25°C	38°			
		0°C	40°			
		70°C	34°			



TLC251, TLC251A, TLC251B, TLC251Y
LinCMOS™ PROGRAMMABLE
LOW-POWER OPERATIONAL AMPLIFIERS

SLOS001F – JULY 1983 – REVISED MARCH 2001

electrical characteristics at specified free-air temperature, $V_{DD} = 1.4\text{ V}$

PARAMETER		TEST CONDITIONS†	T_A ‡	BIAS	TLC251C, TLC251AC, TLC251BC			UNIT
					MIN	TYP	MAX	
V_{IO}	Input offset voltage	$V_O = 0.2\text{ V}$, $R_S = 50\ \Omega$	25°C	Any				mV
					Full range			
			25°C	Any				
					Full range			
			25°C	Any				
					Full range			
$\alpha_{V_{IO}}$	Average temperature coefficient of input offset voltage		25°C to 70°C	Any	1		$\mu\text{V}/^\circ\text{C}$	
I_{IO}	Input offset current	$V_O = 0.2\text{ V}$	25°C	Any	1		pA	
			Full range		300			
I_{IB}	Input bias current	$V_O = 0.2\text{ V}$	25°C	Any	1		pA	
			Full range		600			
V_{ICR}	Common-mode input voltage range		25°C	Any	0 to 0.2		V	
V_{OM}	Peak output voltage swing§	$V_{ID} = 100\text{ mV}$	25°C	Any	450	700	mV	
A_{VD}	Large-signal differential voltage amplification	$V_O = 100\text{ to }300\text{ mV}$, $R_S = 50\ \Omega$	25°C	Low	20			
				High	10			
$CMRR$	Common-mode rejection ratio	$R_S = 50\ \Omega$, $V_{IC} = V_{ICR\text{min}}$	25°C	Any	60	77	dB	
I_{DD}	Supply current	$V_O = 0.2\text{ V}$, No load	25°C	Low	5		μA	
				High	150			

† All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise specified. Unless otherwise noted, an output load resistor is connected from the output to ground and has the following values: for low bias, $R_L = 1\text{ M}\Omega$, for medium bias, $R_L = 100\text{ k}\Omega$, and for high bias, $R_L = 10\text{ k}\Omega$.

‡ Full range is 0°C to 70°C.

§ The output swings to the potential of V_{DD-}/GND .

operating characteristics, $V_{DD} = 1.4\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	BIAS	TLC251C, TLC251AC, TLC251BC			UNIT
				MIN	TYP	MAX	
B_1	Unity-gain bandwidth	$C_L = 100\text{ pF}$	Low	12			kHz
			High	12			
SR	Slew rate at unity gain	See Figure 1	Low	0.001			$\text{V}/\mu\text{s}$
			High	0.1			
	Overshoot factor	See Figure 1	Low	35%			
			High	30%			



TLC251, TLC251A, TLC251B, TLC251Y
LinCMOS™ PROGRAMMABLE
LOW-POWER OPERATIONAL AMPLIFIERS

SLOS001F – JULY 1983 – REVISED MARCH 2001

electrical characteristics, $V_{DD} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	TLC251Y									UNIT
		HIGH-BIAS MODE			MEDIUM-BIAS MODE			LOW-BIAS MODE			
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_O = 1.4\text{ V}$, $V_{IC} = 0\text{ V}$, $R_S = 50\ \Omega$, R_L^\dagger		1.1	10		1.1	10		1.1	10	mV
α_{VIO} Average temperature coefficient of input offset voltage			1.8		1.7		1.1				$\mu\text{V}/^\circ\text{C}$
I_{IO} Input offset current (see Note 4)	$V_O = V_{DD}/2$, $V_{IC} = V_{DD}/2$		0.1	60		0.1	60		0.1	60	pA
I_{IB} Input bias current (see Note 4)	$V_O = V_{DD}/2$, $V_{IC} = V_{DD}/2$		0.6	60		0.6	60		0.6	60	pA
V_{ICR} Common-mode input voltage range (see Note 5)		-0.2 to 4	-0.3 to 4.2		-0.2 to 4	-0.3 to 4.2		-0.2 to 4	-0.3 to 4.2		V
V_{OH} High-level output voltage	$V_{ID} = 100\text{ mV}$, R_L^\dagger	3.2	3.8		3.2	3.9		3.2	4.1		V
V_{OL} Low-level output voltage	$V_{ID} = -100\text{ mV}$, $I_{OL} = 0$		0	50		0	50		0	50	mV
A_{VD} Large-signal differential voltage amplification	$V_O = 0.25\text{ V}$, R_L^\dagger	5	23		25	170		50	480		V/mV
CMRR Common-mode rejection ratio	$V_{IC} = V_{ICRmin}$	65	80		65	91		65	94		dB
k_{SVR} Supply-voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	$V_{DD} = 5\text{ V to }10\text{ V}$, $V_O = 1.4\text{ V}$	65	95		70	93		70	97		dB
$I_{I(SEL)}$ Input current (BIAS SELECT)	$V_{I(SEL)} = V_{DD}/2$		-1.4		-0.13		0.065				μA
I_{DD} Supply current	$V_O = V_{DD}/2$, $V_{IC} = V_{DD}/2$, No load		675	1600		105	280		10	17	μA

† For high-bias mode, $R_L = 10\text{ k}\Omega$; for medium-bias mode, $R_L = 100\text{ k}\Omega$; and for low-bias mode, $R_L = 1\text{ M}\Omega$.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

5. This range also applies to each input individually.



operating characteristics, $V_{DD} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	TLC251Y									UNIT			
		HIGH-BIAS MODE			MEDIUM-BIAS MODE			LOW-BIAS MODE						
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX				
SR	Slew rate at unity gain R_L^\dagger , $C_L = 20\text{ pF}$	$V_I(\text{PP}) = 1\text{ V}$			3.6			0.43			0.03			V/ μs
		$V_I(\text{PP}) = 2.5\text{ V}$			2.9			0.40			0.03			
V_n	Equivalent input noise voltage $f = 1\text{ kHz}$, $R_S = 20\ \Omega$				25			32			68			nV/ $\sqrt{\text{Hz}}$
B_{OM}	Maximum output swing bandwidth $V_O = V_{OH}$, $R_L = 10\text{ k}\Omega$	$C_L = 20\text{ pF}$			320			55			4.5			kHz
B_1	Unity-gain bandwidth $V_I = 10\text{ mV}$, $C_L = 20\text{ pF}$				1700			525			65			kHz
ϕ_m	Phase margin $f = B_1$, $C_L = 20\text{ pF}$	$V_I = 10\text{ mV}$			46°			40°			34°			

† For high-bias mode, $R_L = 10\text{ k}\Omega$; for medium-bias mode, $R_L = 100\text{ k}\Omega$; and for low-bias mode, $R_L = 1\text{ M}\Omega$.

PARAMETER MEASUREMENT INFORMATION

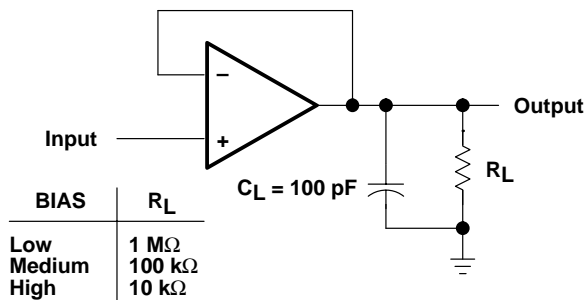


Figure 1. Unity-Gain Amplifier

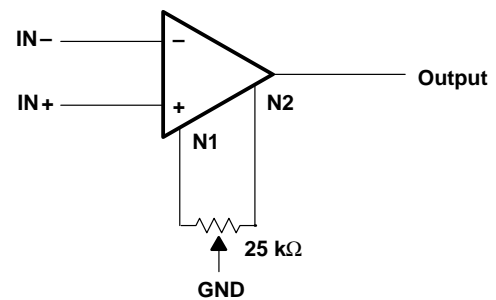


Figure 2. Input Offset Voltage Null Circuit

TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
I_{DD}	Supply current	vs Bias-select voltage	3
		vs Supply voltage	4
		vs Free-air temperature	5
A_{VD}	Large-signal differential voltage amplification	Low bias vs Frequency	6
		Medium bias vs Frequency	7
		High bias vs Frequency	8
	Phase shift	Low bias vs Frequency	6
		Medium bias vs Frequency	7
		High bias vs Frequency	8

TYPICAL CHARACTERISTICS

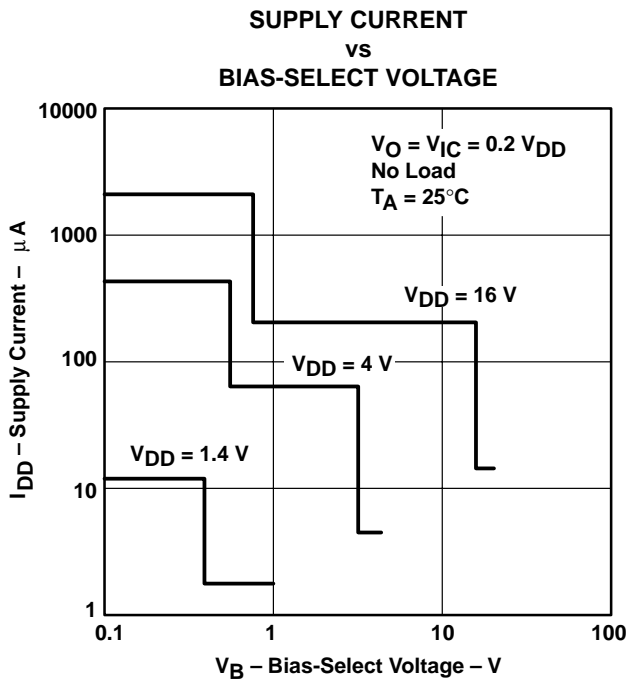


Figure 3

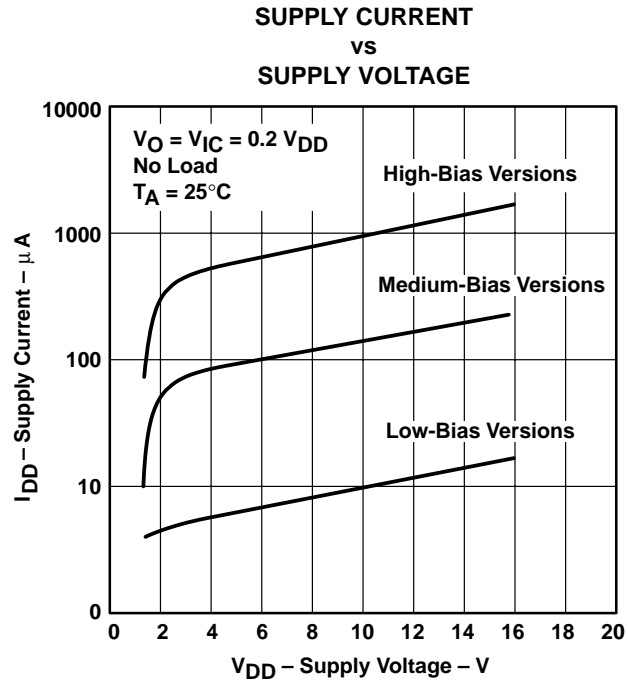


Figure 4

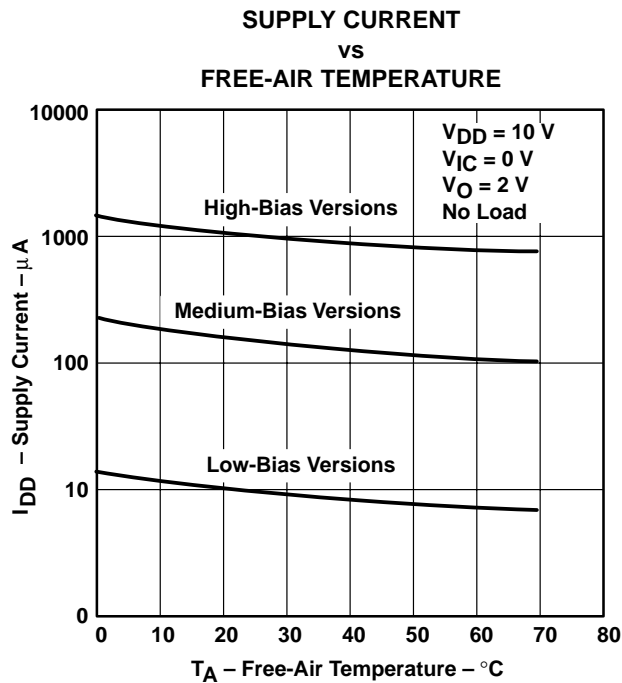


Figure 5

TYPICAL CHARACTERISTICS

**LOW-BIAS LARGE-SIGNAL
 DIFFERENTIAL VOLTAGE AMPLIFICATION
 AND PHASE SHIFT
 vs
 FREQUENCY**

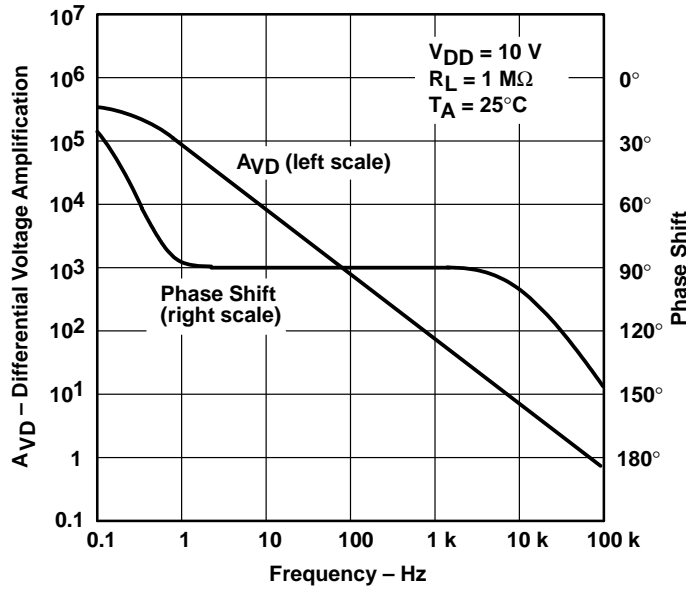


Figure 6

**MEDIUM-BIAS LARGE-SIGNAL
 DIFFERENTIAL VOLTAGE AMPLIFICATION
 AND PHASE SHIFT
 vs
 FREQUENCY**

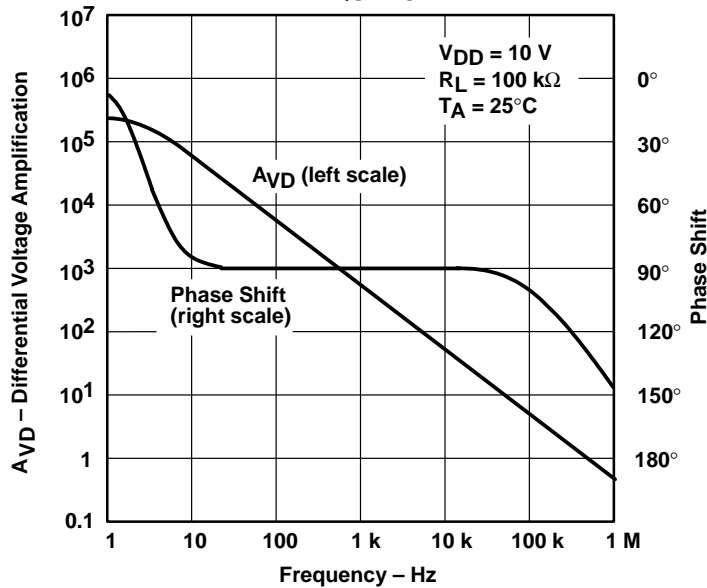


Figure 7

TYPICAL CHARACTERISTICS

HIGH-BIAS LARGE-SIGNAL
DIFFERENTIAL VOLTAGE AMPLIFICATION
AND PHASE SHIFT
vs
FREQUENCY

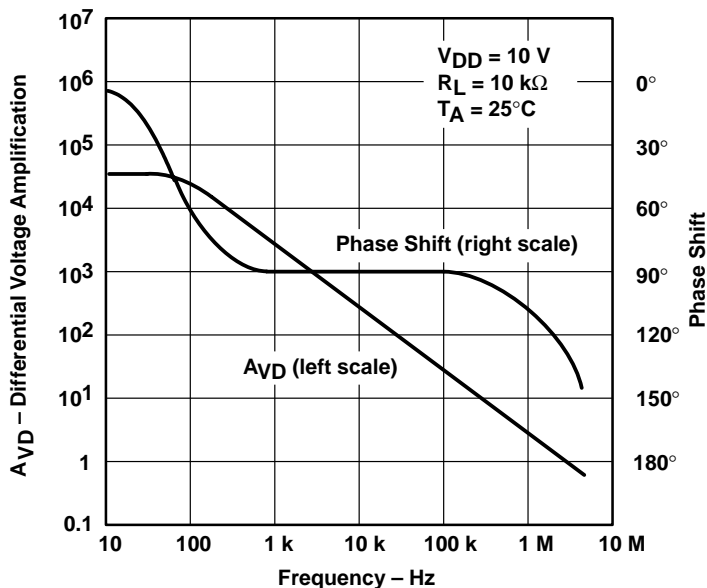


Figure 8

APPLICATION INFORMATION

latch-up avoidance

Junction-isolated CMOS circuits have an inherent parasitic PNP structure that can function as an SCR. Under certain conditions, this SCR may be triggered into a low-impedance state, resulting in excessive supply current. To avoid such conditions, no voltage greater than 0.3 V beyond the supply rails should be applied to any pin. In general, the operational amplifier supplies should be applied simultaneously with, or before, application of any input signals.

APPLICATION INFORMATION

using BIAS SELECT

The TLC251 has a terminal called BIAS SELECT that allows the selection of one of three I_{DD} conditions (10, 150, and 1000 μA typical). This allows the user to trade-off power and ac performance. As shown in the typical supply current (I_{DD}) versus supply voltage (V_{DD}) curves (Figure 4), the I_{DD} varies only slightly from 4 V to 16 V. Below 4 V, the I_{DD} varies more significantly. Note that the I_{DD} values in the medium- and low-bias modes at $V_{DD} = 1.4$ V are typically 2 μA , and in the high mode are typically 12 μA . The following table shows the recommended BIAS SELECT connections at $V_{DD} = 10$ V.

BIAS MODE	AC PERFORMANCE	BIAS SELECT CONNECTION†	TYPICAL $I_{DD}‡$
Low	Low	V_{DD}	10 μA
Medium	Medium	0.8 V to 9.2 V	150 μA
High	High	Ground pin	1000 μA

† Bias selection may also be controlled by external circuitry to conserve power, etc. For information regarding BIAS SELECT, see Figure 3 in the typical characteristics curves.

‡ For I_{DD} characteristics at voltages other than 10 V, see Figure 4 in the typical characteristics curves.

output stage considerations

The amplifier's output stage consists of a source-follower-connected pullup transistor and an open-drain pulldown transistor. The high-level output voltage (V_{OH}) is virtually independent of the I_{DD} selection and increases with higher values of V_{DD} and reduced output loading. The low-level output voltage (V_{OL}) decreases with reduced output current and higher input common-mode voltage. With no load, V_{OL} is essentially equal to the potential of V_{DD-}/GND .

input offset nulling

The TLC251C series offers external offset null control. Nulling may be achieved by adjusting a 25-k Ω potentiometer connected between the offset null terminals with the wiper connected to the device V_{DD-}/GND pin as shown in Figure 2. The amount of nulling range varies with the bias selection. At an I_{DD} setting of 1000 μA (high bias), the nulling range allows the maximum offset specified to be trimmed to zero. In low or medium bias or when the amplifier is used below 4 V, total nulling may not be possible for all units.

supply configurations

Even though the TLC251C series is characterized for single-supply operation, it can be used effectively in a split-supply configuration when the input common-mode voltage (V_{ICR}), output swing (V_{OL} and V_{OH}), and supply voltage limits are not exceeded.

circuit layout precautions

The user is cautioned that whenever extremely high circuit impedances are used, care must be exercised in layout, construction, board cleanliness, and supply filtering to avoid hum and noise pickup, as well as excessive dc leakages.

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
TLC251ACD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC251ACDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC251ACP	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC251ACPE4	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC251BCP	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC251BCPE4	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC251CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC251CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC251CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC251CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC251CP	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC251CPE4	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

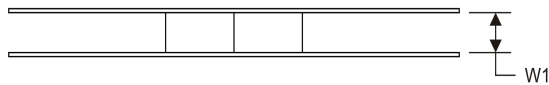
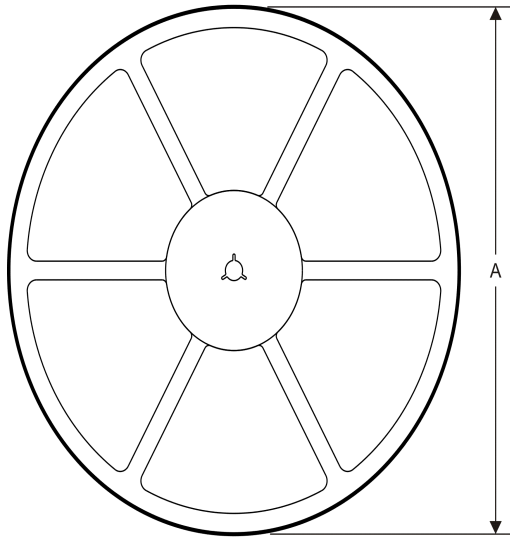
⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

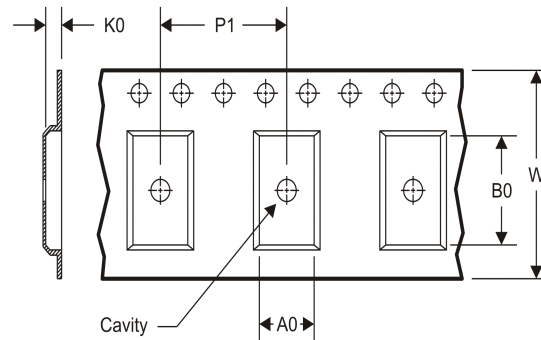
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLC251CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC251CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLC251CDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC251CDR	SOIC	D	8	2500	367.0	367.0	35.0

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46C and to discontinue any product or service per JESD48B. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have **not** been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components which meet ISO/TS16949 requirements, mainly for automotive use. Components which have not been so designated are neither designed nor intended for automotive use; and TI will not be responsible for any failure of such components to meet such requirements.

Products

Audio	www.ti.com/audio
Amplifiers	amplifier.ti.com
Data Converters	dataconverter.ti.com
DLP® Products	www.dlp.com
DSP	dsp.ti.com
Clocks and Timers	www.ti.com/clocks
Interface	interface.ti.com
Logic	logic.ti.com
Power Mgmt	power.ti.com
Microcontrollers	microcontroller.ti.com
RFID	www.ti-rfid.com
OMAP Mobile Processors	www.ti.com/omap
Wireless Connectivity	www.ti.com/wirelessconnectivity

Applications

Automotive and Transportation	www.ti.com/automotive
Communications and Telecom	www.ti.com/communications
Computers and Peripherals	www.ti.com/computers
Consumer Electronics	www.ti.com/consumer-apps
Energy and Lighting	www.ti.com/energy
Industrial	www.ti.com/industrial
Medical	www.ti.com/medical
Security	www.ti.com/security
Space, Avionics and Defense	www.ti.com/space-avionics-defense
Video and Imaging	www.ti.com/video

TI E2E Community e2e.ti.com